

InP Wafer



鼎泰苜源
DT Wafer-Tech

(—) Standard for Crystal Electrical Parameters

| Dopant | Un-InP | S-InP | Sn-InP | Fe-InP | Zn-InP |
|---|-----------------------------|------------------------------|-----------------------------|--------------------|--|
| Conduction | S-C-N | S-C-N | S-C-N | SI | S-C-P |
| Size (inch) | 2/3/4 | 2/3/4 | 2/3/4 | 2/3/4 | 2/3/4 |
| Carrier Concentration (cm ⁻³) | (0.3 ~ 2)×10 ¹⁶ | (1 ~ 8)×10 ¹⁸ | (1 ~ 4)×10 ¹⁸ | — | (0.6 ~ 2)×10 ¹⁸ (3 ~ 6)×10 ¹⁸ |
| Resistivity (Ω·cm) | — | (0.6 ~ 2.5)×10 ⁻³ | (1 ~ 6)×10 ⁻³ | ≥5×10 ⁶ | — |
| Mobility(cm ² /V·s) | (3.5 ~ 4.5)×10 ³ | (1 ~ 2)×10 ³ | (1.2 ~ 2.1)×10 ³ | ≥2×10 ³ | 70 ~ 90 50 ~ 70 |
| EPD (cm ⁻²) | 2" : ≤1000 | 2" : ≤500 | 2" : ≤5000 | 2" : ≤5000 | 2" : ≤1000 |
| | 3" : ≤1000 | 3" : ≤1000 | 3" : ≤5000 | 3" : ≤5000 | 3" : ≤1000 |
| | 4" : ≤5000 | 4" : ≤5000 | 4" : ≤10000 | 4" : ≤5000 | 4" : ≤5000 |



material_sales@ostech.co.jp



http://www.ostech.co.jp



5-2-27, Minami-mikunigaoka, Sakai-ku, Sakai, Osaka, JAPAN 590-0023

TEL : +81-72-221-2778 FAX : +81-72-221-2779



InP Wafer



鼎泰苜源
DT Wafer-Tech

(二) Standard for Processing Parameters

| Specifications | | 2 inch | 3 inch | 4 inch |
|--|-------------|------------|----------|-----------|
| Orientation | | (100)±0.3° | | |
| Diameter (mm) | | 50.5±0.4 | 76.2±0.3 | 100.0±0.3 |
| Thickness (μm) | | 350±25 | 600±25 | 625±25 |
| Primary Flat Length (mm) | | 16.0±1.0 | 22.0±1.0 | 32.5±1.0 |
| Secondary Flat Length (mm) | | 7.0±1.0 | 12.0±1.0 | 18.0±1.0 |
| Flatness | TTV (μm) | < 10 | < 10 | < 15 |
| | TIR (μm) | < 10 | < 10 | < 15 |
| | Bow (μm) | < 10 | < 10 | < 15 |
| | Warp (μm) | < 15 | < 15 | < 15 |
| PE/PP, Epi-ready; Special size can be customized | | | | |

